

# Sheng-Shi Li

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

43  
papers

1,561  
citations

21  
h-index

39  
g-index

45  
ext. papers

1,748  
ext. citations

4.5  
avg. IF

4.72  
L-index

#	Paper	IF	Citations
43	Magnetic tuning in a novel half-metallic Ir <sub>2</sub> Te <sub>2</sub> monolayer. <i>Journal of Semiconductors</i> , <b>2022</b> , 43, 052001	2.3	0
42	Two-dimensional Weyl semi-half-metallic NiCS with a band structure controllable by the direction of magnetization. <i>Physical Chemistry Chemical Physics</i> , <b>2021</b> , 23, 12068-12074	3.6	5
41	Glide Mirror Plane Protected Nodal-Loop in an Anisotropic Half-Metallic MnNF Monolayer. <i>Journal of Physical Chemistry Letters</i> , <b>2020</b> , 11, 485-491	6.4	15
40	Discovery of a ferroelastic topological insulator in a two-dimensional tetragonal lattice. <i>Physical Chemistry Chemical Physics</i> , <b>2019</b> , 21, 5165-5169	3.6	4
39	Bismuth oxide film: a promising room-temperature quantum spin Hall insulator. <i>Journal of Physics Condensed Matter</i> , <b>2018</b> , 30, 105303	1.8	4
38	Robust half-metallicity in transition metal tribromide nanowires. <i>Nanoscale</i> , <b>2018</b> , 10, 15545-15552	7.7	11
37	Distorted Janus Transition Metal Dichalcogenides: Stable Two-Dimensional Materials with Sizable Band Gap and Ultrahigh Carrier Mobility. <i>Journal of Physical Chemistry C</i> , <b>2018</b> , 122, 19153-19160	3.8	32
36	Discovery of Two-Dimensional Quantum Spin Hall Effect in Triangular Transition-Metal Carbides. <i>Chinese Physics Letters</i> , <b>2018</b> , 35, 087303	1.8	2
35	Discovery of a novel spin-polarized nodal ring in a two-dimensional HK lattice. <i>Nanoscale</i> , <b>2018</b> , 10, 20748-20753	7.7	37
34	Prediction of high-temperature Chern insulator with half-metallic edge states in asymmetry-functionalized stanene. <i>Nanoscale</i> , <b>2018</b> , 10, 20226-20233	7.7	74
33	High-temperature Dirac half-metal PdCl <sub>3</sub> : a promising candidate for realizing quantum anomalous Hall effect. <i>Journal of Materials Chemistry C</i> , <b>2018</b> , 6, 10284-10291	7.1	37
32	Prediction of tunable quantum spin Hall effect in methyl-functionalized tin film. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 2656-2661	7.1	14
31	Tunability of the Quantum Spin Hall Effect in Bi(110) Films: Effects of Electric Field and Strain Engineering. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 21515-21523	9.5	20
30	Discovery of intrinsic quantum anomalous Hall effect in organic Mn-DCA lattice. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 233107	3.4	52
29	Two-dimensional arsenene oxide: A realistic large-gap quantum spin Hall insulator. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 213101	3.4	100
28	Prediction of topological crystalline insulators and topological phase transitions in two-dimensional PbTe films. <i>Physical Chemistry Chemical Physics</i> , <b>2017</b> , 19, 29647-29652	3.6	6
27	Unconventional band inversion and intrinsic quantum spin Hall effect in functionalized group-V binary films. <i>Scientific Reports</i> , <b>2017</b> , 7, 6126	4.9	13

26	Two-dimensional GaGeTe film: a promising graphene-like material with tunable band structure and high carrier mobility. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 8847-8853	7.1	13
25	Intrinsic Dirac half-metal and quantum anomalous Hall phase in a hexagonal metal-oxide lattice. <i>Physical Review B</i> , <b>2017</b> , 96,	3.3	112
24	Effect of Amidogen Functionalization on Quantum Spin Hall Effect in Bi/Sb(111) Films. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 41443-41453	9.5	101
23	Emergence of ferrimagnetic half-metallicity in two-dimensional MXene Mo <sub>3</sub> N <sub>2</sub> F <sub>2</sub> . <i>Applied Physics Letters</i> , <b>2017</b> , 111, 202405	3.4	18
22	Hydrogenated group-IV binary monolayers: a new family of inversion-asymmetric topological insulators. <i>RSC Advances</i> , <b>2016</b> , 6, 79452-79458	3.7	2
21	Functionalized Thallium Antimony Films as Excellent Candidates for Large-Gap Quantum Spin Hall Insulator. <i>Scientific Reports</i> , <b>2016</b> , 6, 21351	4.9	25
20	Room Temperature Quantum Spin Hall Insulator in Ethynyl-Derivative Functionalized Stanene Films. <i>Scientific Reports</i> , <b>2016</b> , 6, 18879	4.9	48
19	New family of room temperature quantum spin Hall insulators in two-dimensional germanene films. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 2088-2094	7.1	66
18	Unexpected Giant-Gap Quantum Spin Hall Insulator in Chemically Decorated Plumbene Monolayer. <i>Scientific Reports</i> , <b>2016</b> , 6, 20152	4.9	131
17	Large-gap quantum spin Hall state in functionalized dumbbell stanene. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 073104	3.4	77
16	Robust Room-Temperature Quantum Spin Hall Effect in Methyl-functionalized InBi honeycomb film. <i>Scientific Reports</i> , <b>2016</b> , 6, 23242	4.9	22
15	Silicon-based chalcogenide: Unexpected quantum spin Hall insulator with sizable band gap. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 182109	3.4	62
14	Controllable electronic and magnetic properties in a two-dimensional germanene heterostructure. <i>Physical Chemistry Chemical Physics</i> , <b>2016</b> , 18, 12169-74	3.6	10
13	Robust room-temperature inversion-asymmetry topological transitions in functionalized HgSe monolayer. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 2243-2251	7.1	20
12	Electronic structure and optical properties of Bi,N co-doped SnO <sub>2</sub> . <i>Journal of Materials Science</i> , <b>2015</b> , 50, 6993-6999	4.3	15
11	Ethynyl-functionalized stanene film: a promising candidate as large-gap quantum spin Hall insulator. <i>New Journal of Physics</i> , <b>2015</b> , 17, 083036	2.9	139
10	First-principles design of silicene/Sc <sub>2</sub> CF <sub>2</sub> heterojunction as a promising candidate for field effect transistor. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 085306	2.5	21
9	Silicane as an Inert Substrate of Silicene: A Promising Candidate for FET. <i>Journal of Physical Chemistry C</i> , <b>2014</b> , 118, 25278-25283	3.8	55

8	Tunable electronic properties induced by a defect-substrate in graphene/BC3 heterobilayers. <i>Physical Chemistry Chemical Physics</i> , <b>2014</b> , 16, 22861-6	3.6	26
7	Tunable electronic and magnetic properties in germanene by alkali, alkaline-earth, group III and 3d transition metal atom adsorption. <i>Physical Chemistry Chemical Physics</i> , <b>2014</b> , 16, 15968-78	3.6	56
6	Novel band structures in silicene on monolayer zinc sulfide substrate. <i>Journal of Physics Condensed Matter</i> , <b>2014</b> , 26, 395003	1.8	12
5	First-principles study of AlN nanosheets with chlorination. <i>RSC Advances</i> , <b>2014</b> , 4, 7500	3.7	17
4	Prediction of half-metallic ferromagnetism in C-doped CdS nanowire. <i>RSC Advances</i> , <b>2014</b> , 4, 24399	3.7	8
3	Novel half-metal and spin gapless semiconductor properties in N-doped silicene nanoribbons. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 154302	2.5	36
2	First-principles study on ferromagnetism in W-doped graphene. <i>RSC Advances</i> , <b>2013</b> , 3, 26261	3.7	18
1	First-principles study of graphene adsorbed on WS2 monolayer. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 183709	2.5	21